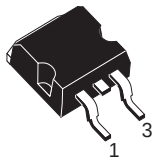
STB100NH02L

N-CHANNEL 24V - 0.0052 Ω - 60A D²PAK
STripFET™ III POWER MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STB100NH02L	24 V	< 0.006 Ω	60 A (2)

- TYPICAL R_{DS}(on) = 0.0052 Ω @ 10 V
- TYPICAL R_{DS}(on) = 0.007 Ω @ 5 V
- $R_{DS(ON)}$ * Qg INDUSTRY's BENCHMARK
- CONDUCTION LOSSES REDUCED
- SWITCHING LOSSES REDUCED
- LOW THRESHOLD DEVICE
- SURFACE-MOUNTING D²PAK (TO-263) POWER PACKAGE IN TUBE (NO SUFFIX) OR IN TAPE & REEL (SUFFIX "T4")

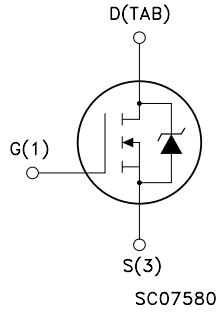


D²PAK
TO-263
(Suffix "T4")

DESCRIPTION
The STB100NH02L utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable fot the most demanding DC-DC converter applications where high efficiency is to be achieved.

APPLICATIONS
- SPECIFICALLY DESIGNED AND OPTIMISED FOR HIGH EFFICIENCY DC/DC CONVERTERS

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{spike(1)}$	Drain-source Voltage Rating	30	V
V_{DS}	Drain-source Voltage (V_{GS} = 0)	24	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	24	V
V_{GS}	Gate- source Voltage	± 20	V
I_D(2)	Drain Current (continuous) at T_C = 25°C	60	A
I_D(2)	Drain Current (continuous) at T_C = 100°C	60	A
I_{DM}(3)	Drain Current (pulsed)	240	A
P_{tot}	Total Dissipation at T_C = 25°C	100	W
	Derating Factor	0.67	W/°C
E_{AS} (4)	Single Pulse Avalanche Energy	600	mJ
T_{stg}	Storage Temperature	-55 to 175	°C
T_j	Max. Operating Junction Temperature		

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	1.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300	°C

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 25 mA, V_{GS} = 0	24			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = 20 V V_{DS} = 20 V T_C = 125°C			1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			±100	nA

ON (5)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	1	1.8		V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 30 A V_{GS} = 5 V I_D = 15 A		0.0052 0.007	0.006 0.011	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (5)	Forward Transconductance	V_{DS} = 10 V I_D = 30 A		40		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 15V f = 1 MHz V_{GS} = 0		2850 800 120		pF pF pF
R_G	Gate Input Resistance	f=1 MHz Gate DC Bias=0 Test Signal Level =20 mV Open Drain		1		Ω

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 10 V I_D =30 A R_G = 4.7 Ω V_{GS} = 10 V (Resistive Load, Figure 3)		13 75		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD}=10 V I_D=60 A V_{GS}=10 V		47.5 10 7	64	nC nC nC

SWITCHING OFF

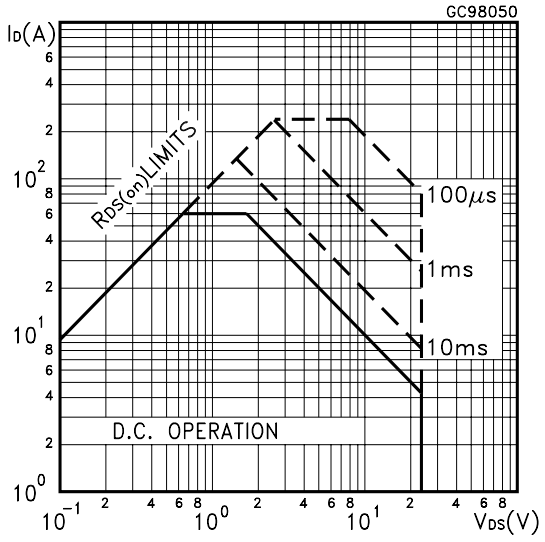
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 10 V I_D = 30 A R_G = 4.7Ω, V_{GS} = 10 V (Resistive Load, Figure 3)		50 18	 24.3	ns ns

SOURCE DRAIN DIODE

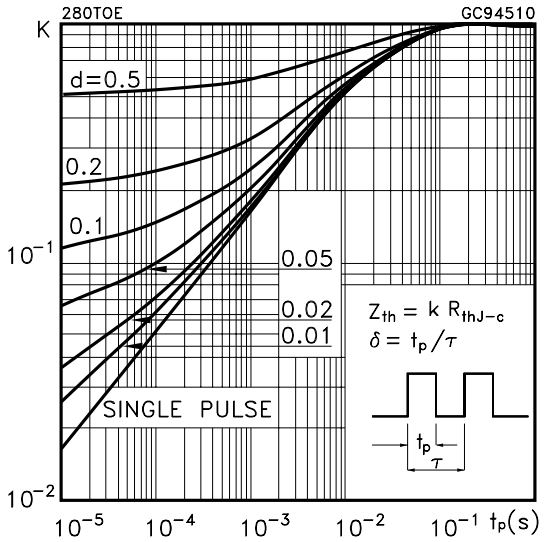
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}	Source-drain Current Source-drain Current (pulsed)				60 240	A A
V_{SD} (5)	Forward On Voltage	I_{SD} = 30 A V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 60 A di/dt = 100A/µs V_{DD} = 16 V T_j = 150°C (see test circuit, Figure 5)		35 35 2		ns nC A

(1) Garanted when external Rg=4.7 Ω and $t_f < t_{fmax}$.
(2) Value limited by wire bonding
(3) Pulse width limited by safe operating area.
(4) Starting T_j = 25 °C, I_D = 30A, V_{DD} = 15V
(5) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
(6) $Q_{oss} = C_{oss}{}^{*}\Delta V_{in}$, $C_{oss} = C_{gd} + C_{ds}$. See Appendix A
(7) Gate charge for synchronous operation

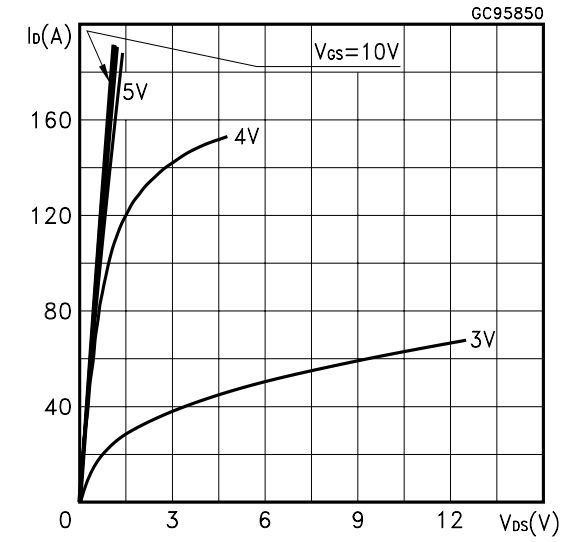
Safe Operating Area



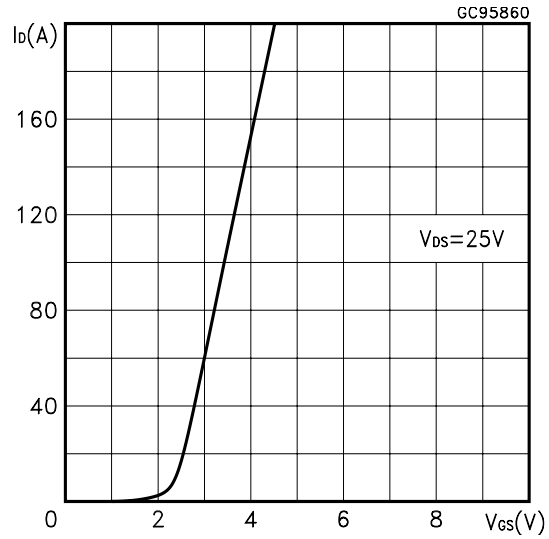
Thermal Impedance



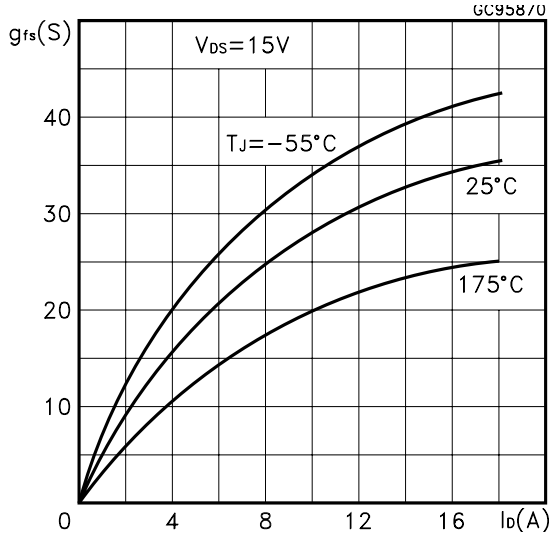
Output Characteristics



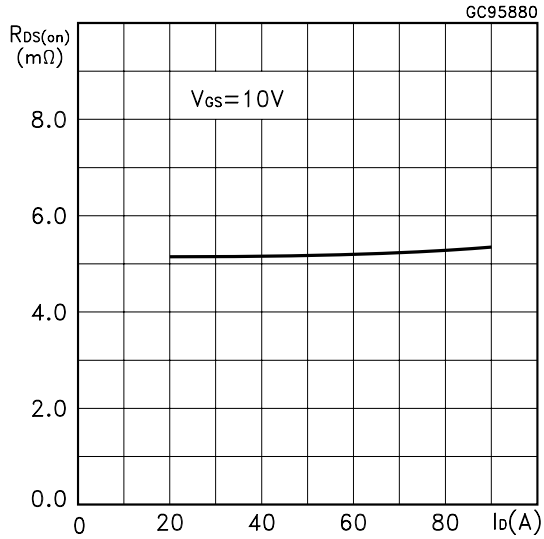
Transfer Characteristics



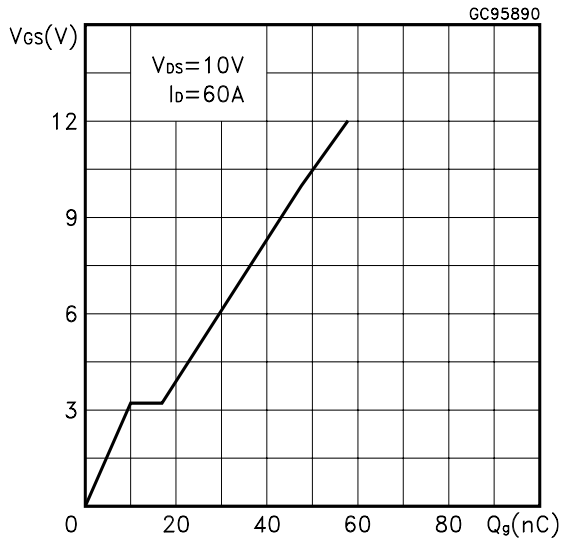
Transconductance



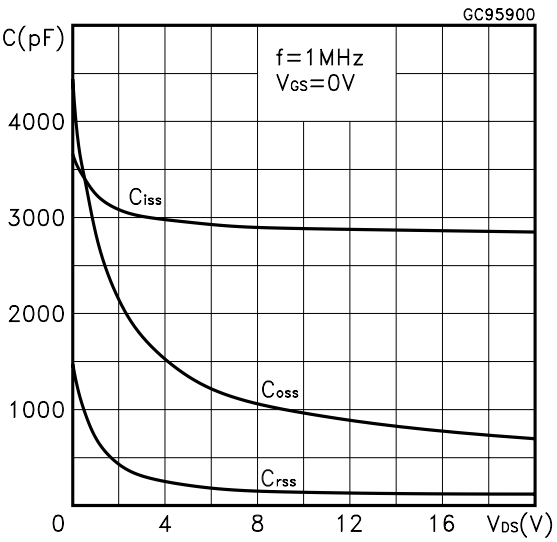
Static Drain-source On Resistance



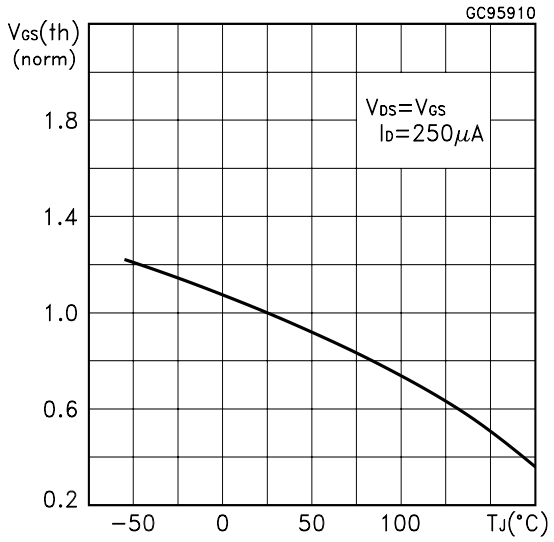
Gate Charge vs Gate-source Voltage



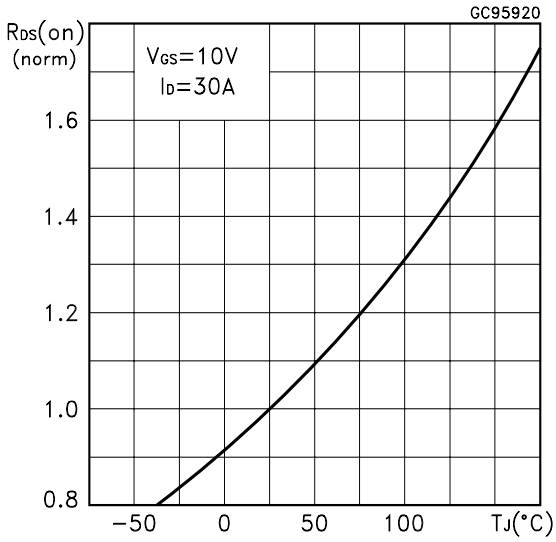
Capacitance Variations



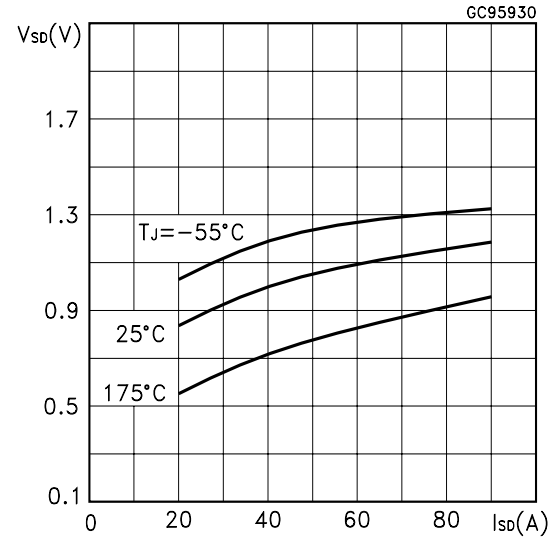
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

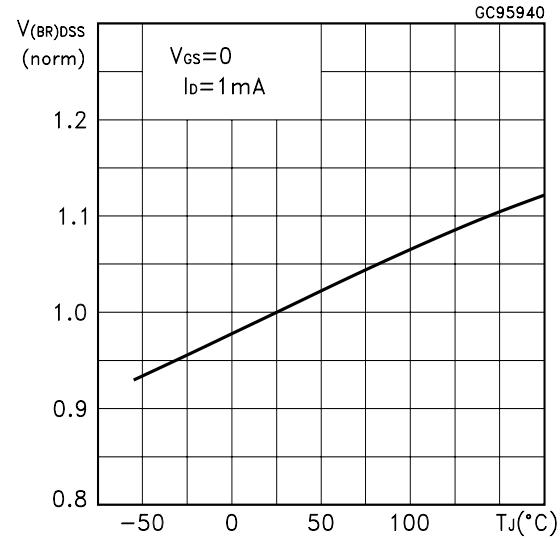


Fig. 1: Unclamped Inductive Load Test Circuit

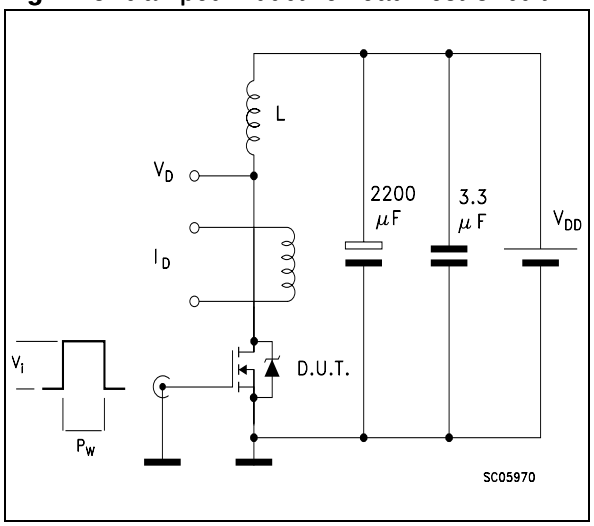


Fig. 2: Unclamped Inductive Waveform

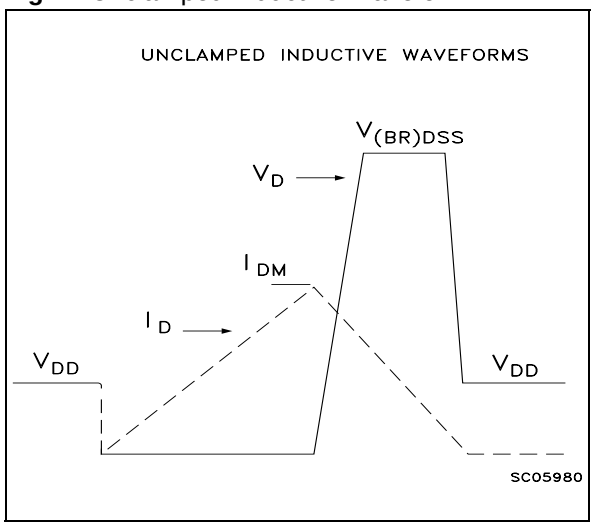


Fig. 3: Switching Times Test Circuits For Resistive Load

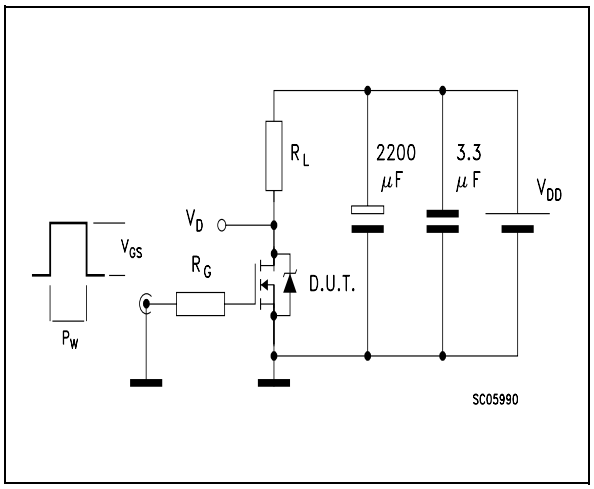


Fig. 4: Gate Charge test Circuit

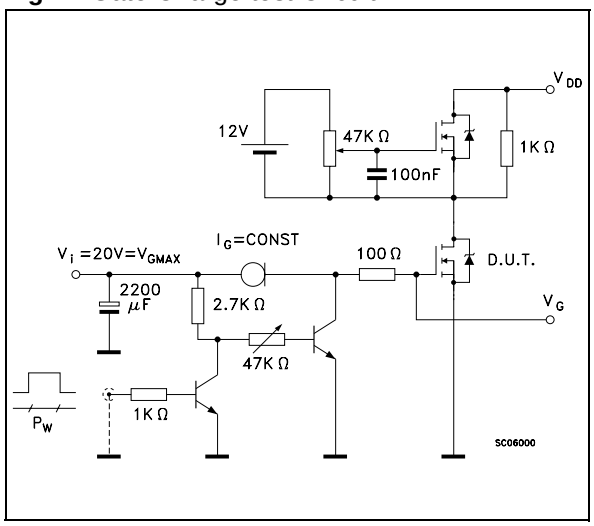
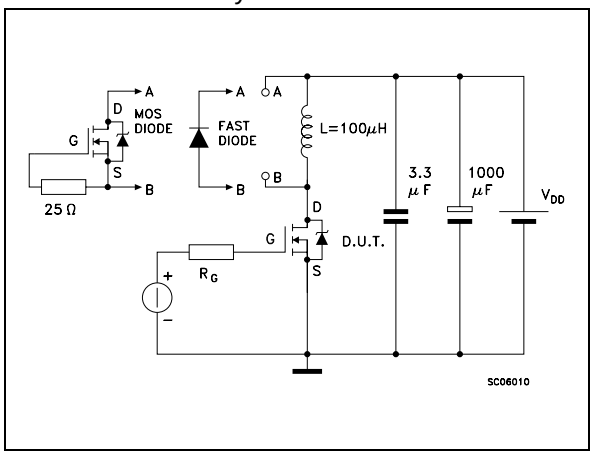
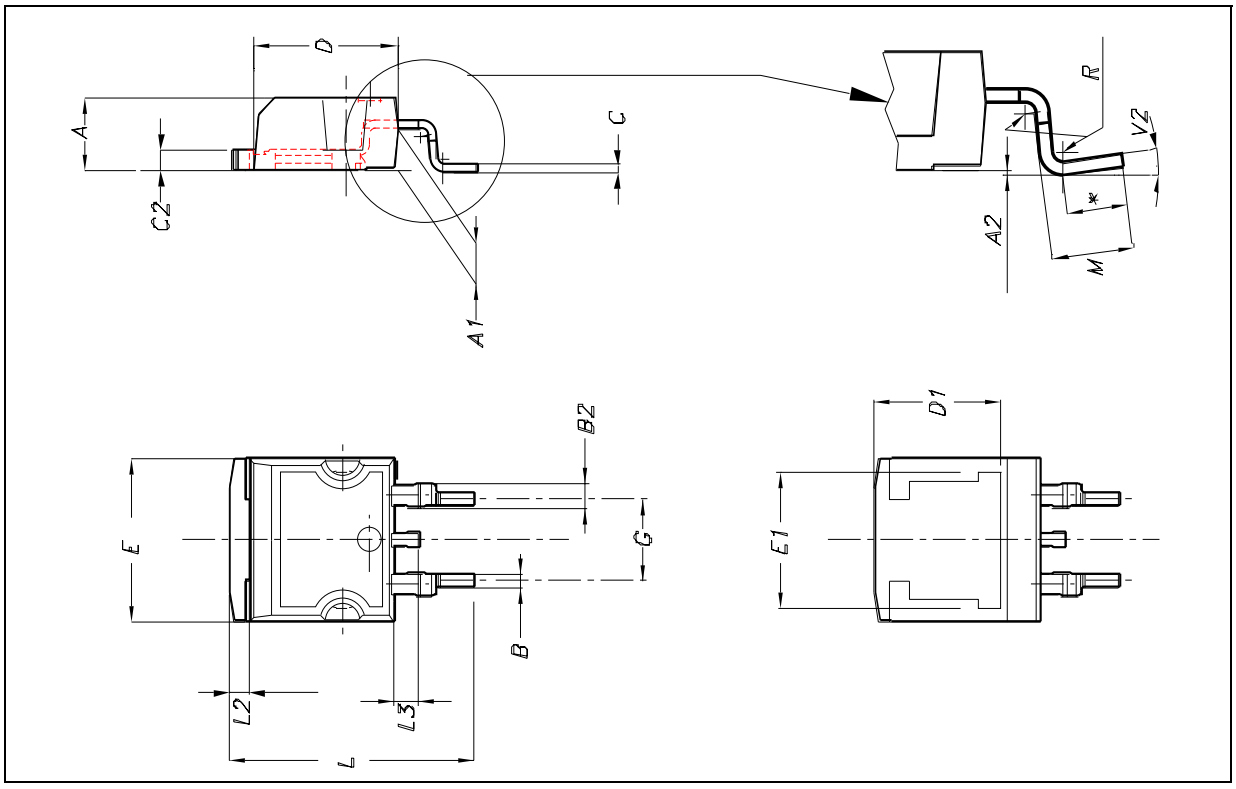


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

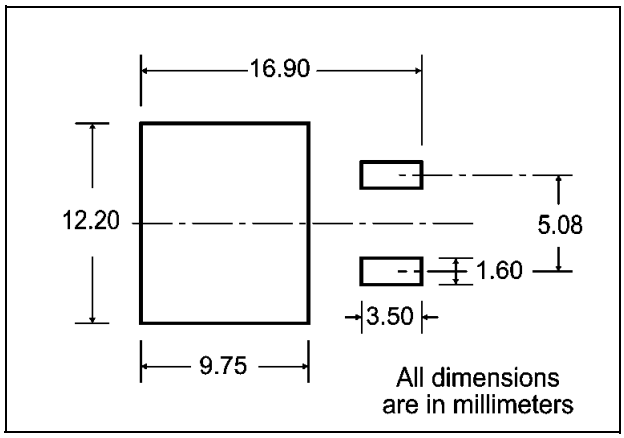


D²PAK MECHANICAL DATA

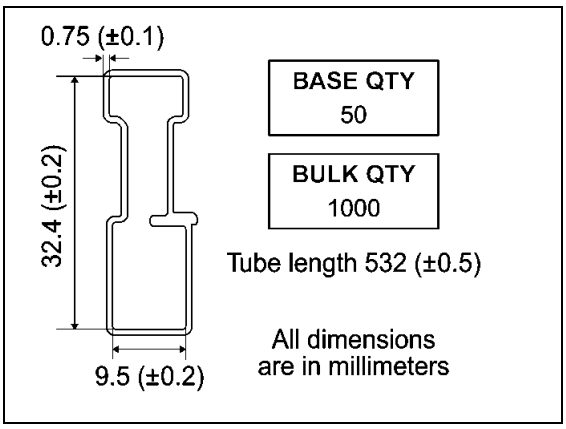
DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°	0°		4°



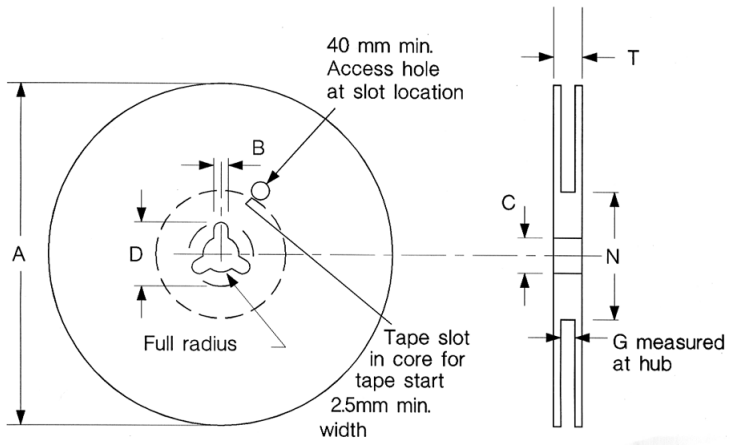
D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



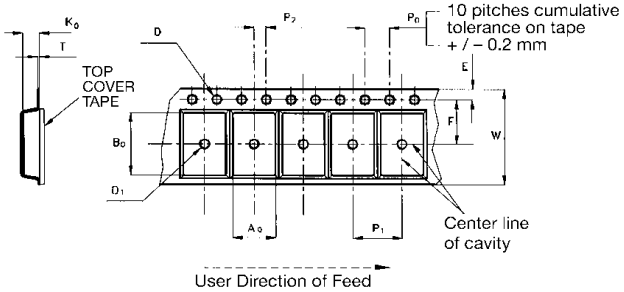
REEL MECHANICAL DATA

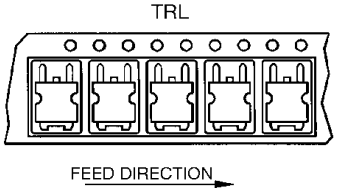
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

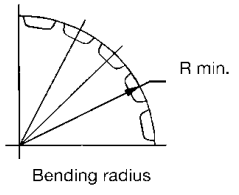
BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0075	0.082
R	50		1.574	
T	0.25	0.35	.0.0098	0.0137
W	23.7	24.3	0.933	0.956

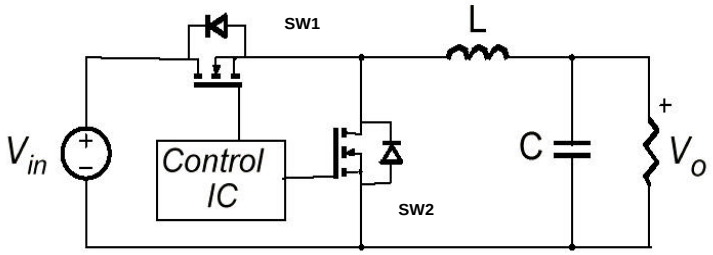






* on sales type

APPENDIX A
Buck Converter: Power Losses Estimation



The power losses associated with the FETs in a Synchronous Buck converter can be estimated using the equations shown in the table below. The formulas give a good approximation, for the sake of performance comparison, of how different pairs of devices affect the converter efficiency. However a very important parameter, the working temperature, is not considered. The real device behavior is really dependent on how the heat generated inside the devices is removed to allow for a safer working junction temperature.
The low side (**SW2**) device requires:

- Very low $R_{DS(on)}$ to reduce conduction losses
- Small Q_{gls} to reduce the gate charge losses
- Small C_{oss} to reduce losses due to output capacitance
- Small Q_{rr} to reduce losses on SW_1 during its turn-on
- The C_{gd}/C_{gs} ratio lower than V_{th}/V_{gg} ratio especially with low drain to source voltage to avoid the cross conduction phenomenon;

The high side (**SW1**) device requires:

- Small R_g and L_s to allow higher gate current peak and to limit the voltage feedback on the gate
- Small Q_g to have a faster commutation and to reduce gate charge losses
- Low $R_{DS(on)}$ to reduce the conduction losses.

		High Side Switch (SW1)	Low Side Switch (SW2)
$P_{conduction}$		$R_{DS(on)SW1} * I_L^2 * d$	$R_{DS(on)SW2} * I_L^2 * (1-d)$
$P_{switching}$		$V_{in} * (Q_{gsth(SW1)} + Q_{gd(SW1)}) * f * \frac{I_L}{I_g}$	Zero Voltage Switching
P_{diode}	Recovery	Not Applicable	[1] $V_{in} * Q_{rr(SW2)} * f$
	Conduction	Not Applicable	$V_{f(SW2)} * I_L * t_{deadtime} * f$
$P_{gate(Q_G)}$		$Q_{g(SW1)} * V_{gg} * f$	$\mathbf{Q_{gls(SW2)} * V_{gg} * f}$
P_{Qoss}		$\frac{V_{in} * Q_{oss(SW1)} * f}{2}$	$\frac{V_{in} * Q_{oss(SW2)} * f}{2}$

Parameter	**Meaning**
d	Duty-cycle
Q_{gsth}	Post threshold gate charge
Q_{gls}	Third quadrant gate charge
Pconduction	On state losses
Pswitching	On-off transition losses
Pdiode	Conduction and reverse recovery diode losses
Pgate	Gate drive losses
P_{Qoss}	Output capacitance losses

[1] Dissipated by SW1 during turn-on

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